

## N-Channel Reduced $Q_g$ , Fast Switching MOSFET

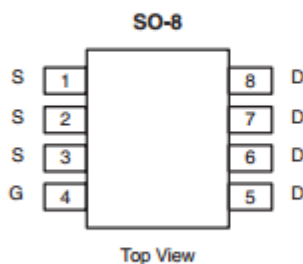
PRODUCT SUMMARY		
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
60	0.022 at $V_{GS} = 10$ V	8.5
	0.031 at $V_{GS} = 4.5$ V	7.2

### FEATURES

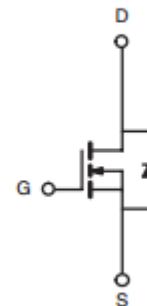
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFETs
- 175 °C Maximum Junction Temperature
- Compliant to RoHS Directive 2002/95/EC



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
Available



Ordering Information: Si4850EY-T1-E3 (Lead (Pb)-free)  
Si4850EY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted					
Parameter	Symbol	10 s	Steady State	Unit	
Drain-Source Voltage	$V_{DS}$	60		V	
Gate-Source Voltage	$V_{GS}$	$\pm 20$			
Continuous Drain Current ( $T_J = 175$ °C) <sup>a</sup>	$I_D$	$T_A = 25$ °C	8.5	6.0	A
		$T_A = 70$ °C	7.1	5.0	
Pulsed Drain Current	$I_{DM}$	40		mJ	
Avalanche Current	$I_{AS}$	15			
Single Pulse Avalanche Energy	$E_{AS}$	11		W	
Maximum Power Dissipation <sup>a</sup>	$P_D$	$T_A = 25$ °C	3.3		1.7
		$T_A = 70$ °C	2.3	1.2	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 175		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	$t \leq 10$ s	$R_{thJA}$	36	45	°C/W
	Steady State		75	90	
Maximum Junction-to-Foot (Drain)	Steady State	$R_{thJF}$	17	20	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

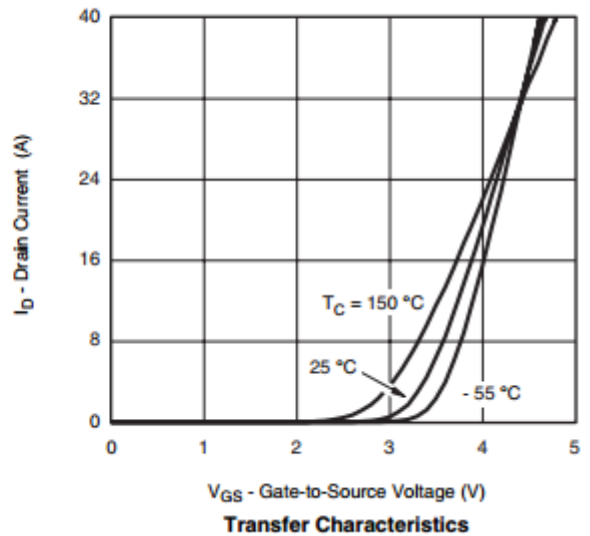
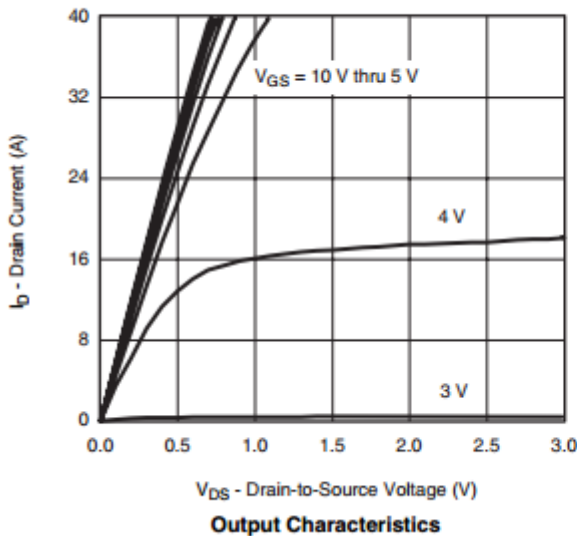
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	60			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1		3	V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			20	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	40			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 6.0\text{ A}$		0.018	0.022	$\Omega$
		$V_{GS} = 10\text{ V}, I_D = 6.0\text{ A}, T_J = 125\text{ }^\circ\text{C}$		0.031	0.037	
		$V_{GS} = 10\text{ V}, I_D = 6.0\text{ A}, T_J = 175\text{ }^\circ\text{C}$		0.039	0.047	
		$V_{GS} = 4.5\text{ V}, I_D = 5.1\text{ A}$		0.025	0.031	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 6.0\text{ A}$		25		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = 1.7\text{ A}, V_{GS} = 0\text{ V}$		0.8	1.2	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = 30\text{ V}, V_{GS} = 10\text{ V}, I_D = 6.0\text{ A}$		18	27	nC
Gate-Source Charge	$Q_{gs}$			3.4		
Gate-Drain Charge	$Q_{gd}$			5.3		
Gate Resistance	$R_g$	$V_{GS} = 0.1\text{ V}, f = 5\text{ MHz}$	0.5	1.4	2.4	$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 30\text{ V}, R_L = 30\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 6\text{ }\Omega$		10	20	ns
Rise Time	$t_r$			10	20	
Turn-Off Delay Time	$t_{d(off)}$			25	50	
Fall Time	$t_f$			12	24	
Source-Drain Reverse Recovery Time	$t_{rr}$	$I_F = 1.7\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		50	80	

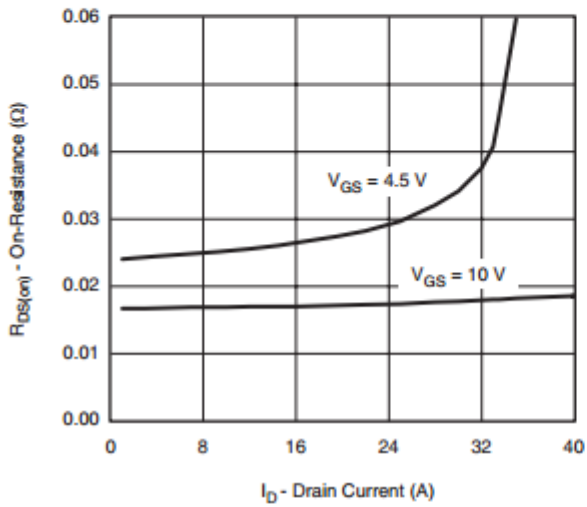
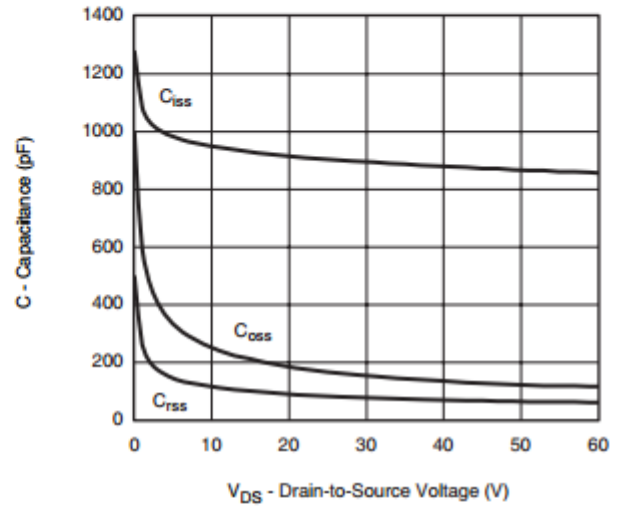
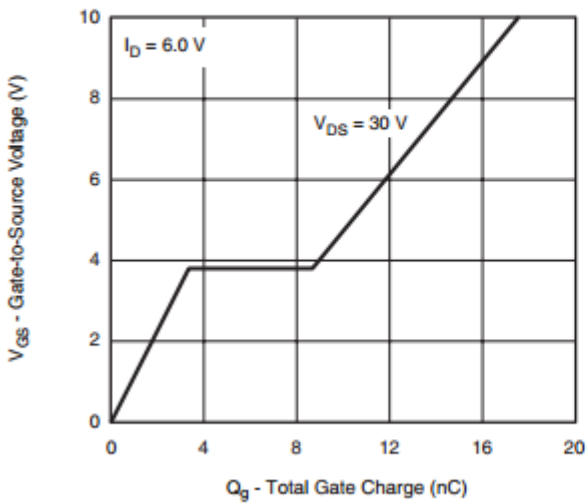
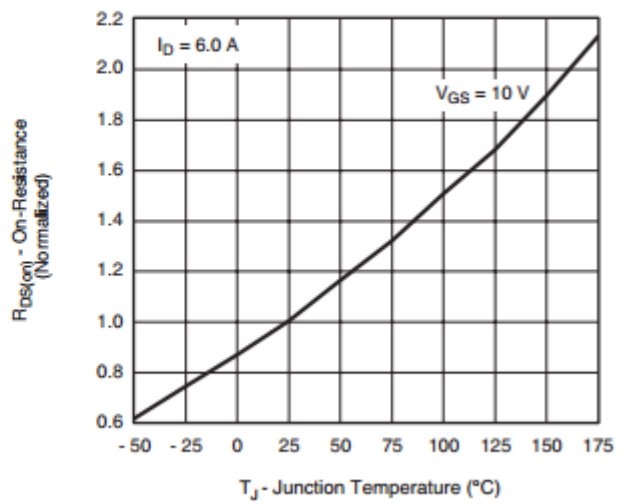
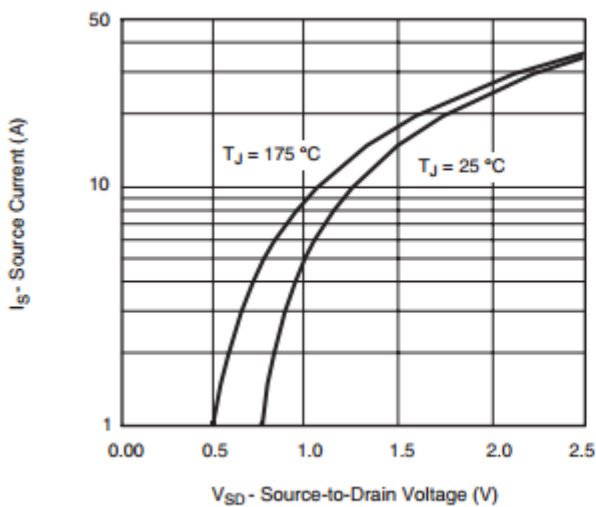
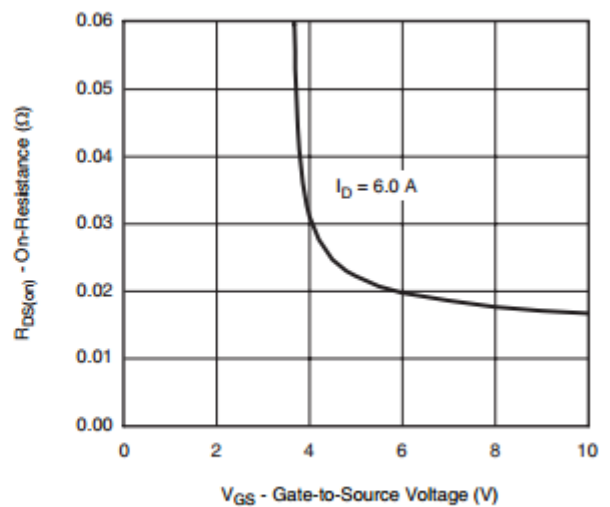
Notes:

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- b. Guaranteed by design, not subject to production testing.

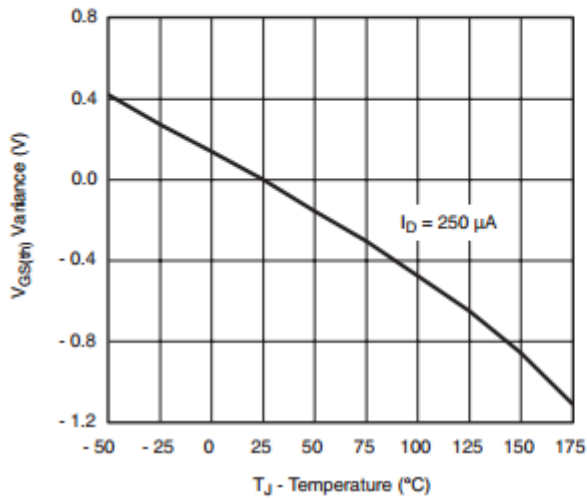
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS**  $25\text{ }^\circ\text{C}$ , unless otherwise noted

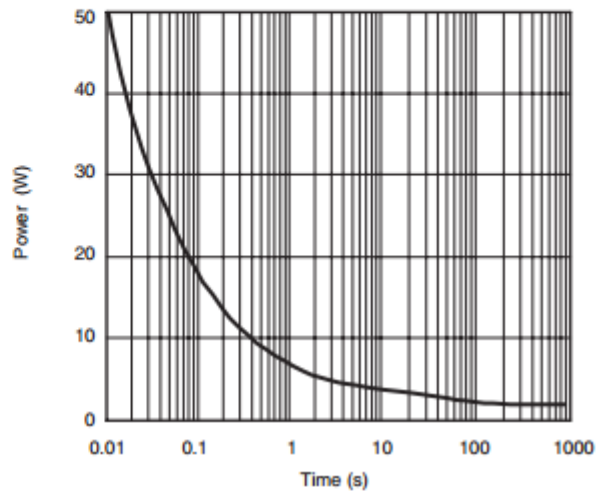


**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

**On-Resistance vs. Drain Current**

**Capacitance**

**Gate Charge**

**On-Resistance vs. Junction Temperature**

**Source-Drain Diode Forward Voltage**

**On-Resistance vs. Gate-to-Source Voltage**

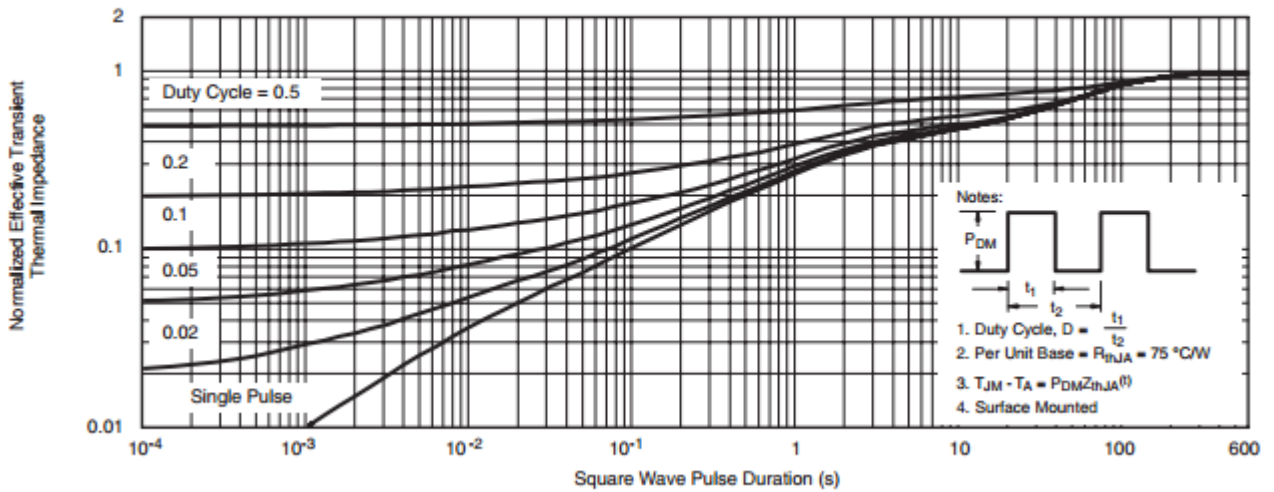
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



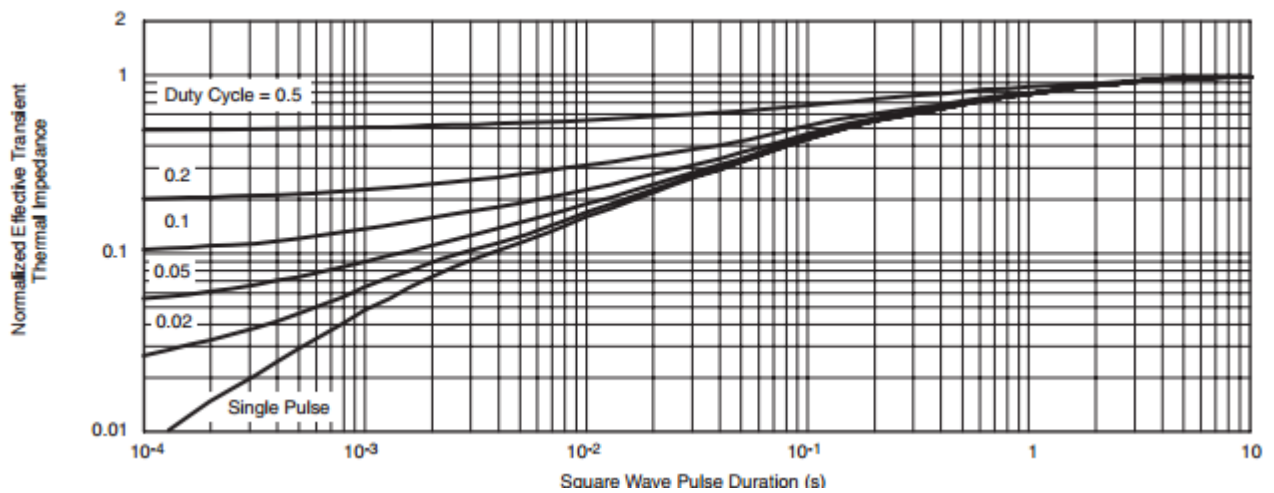
**Threshold Voltage**



**Single Pulse Power**

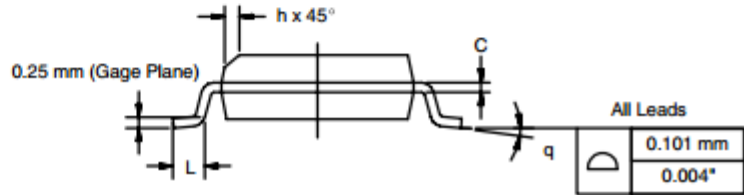
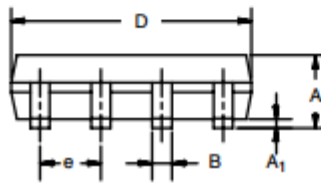
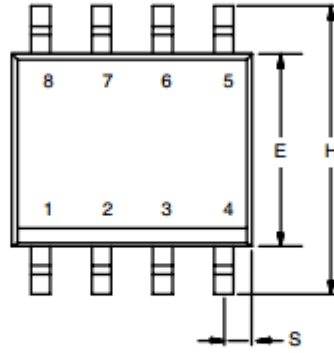


**Normalized Thermal Transient Impedance, Junction-to-Ambient**



# SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A <sub>1</sub>	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				